



## SSC8164GS6

### N-Channel Small Switching MOSFET with ESD Protection

#### ➤ Features

$V_{DS}$	$V_{GS}$	$R_{DS(ON)}$ Typ.	$I_D$	ESD
60V	$\pm 20V$	1.1 $\Omega$ @10V	0.5A	500V
		1.5 $\Omega$ @4.5V		

#### ➤ Description

This device is an N-Channel enhancement mode MOSFET which is produced with high cell density and DMOS trench technology. This device particularly suits low voltage applications, especially for battery powered circuits, the tiny and thin outline saves PCB consumption.

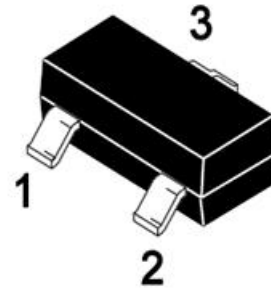
#### ➤ Applications

- Load Switch
- Portable Devices
- DCDC Conversion

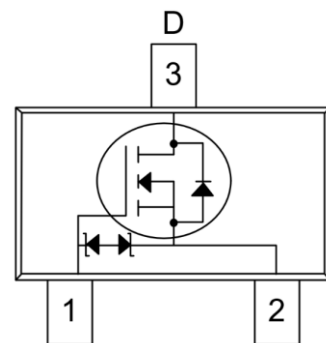
#### ➤ Ordering Information

Device	Package	Shipping	MSL
SSC8164GS6	SOT-23	3000/Reel	3

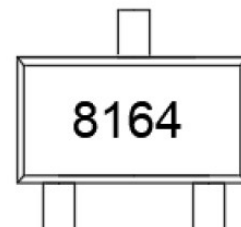
#### ➤ Pin configuration



SOT-23



Pin Configuration (Top View)



Marking



➤ **Absolute Maximum Ratings ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)**

Symbol	Parameter	Ratings	Unit
$V_{DSS}$	Drain-to-Source Voltage	60	V
$V_{GSS}$	Gate-to-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current <sup>a</sup>	0.5	A
$I_{DM}$	Pulsed Drain Current <sup>b</sup>	1	A
$P_D$	Power Dissipation <sup>c</sup>	0.85	W
$P_{DSM}$	Power Dissipation <sup>a</sup>	0.36	W
$T_J$	Operation junction temperature	-55~150	$^{\circ}\text{C}$
$T_{STG}$	Storage temperature range	-55~150	$^{\circ}\text{C}$

➤ **Thermal Resistance Ratings ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)**

Symbol	Parameter	Typical	Maximum	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance <sup>a</sup>		360	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Junction-to-Case Thermal Resistance		155	

Note:

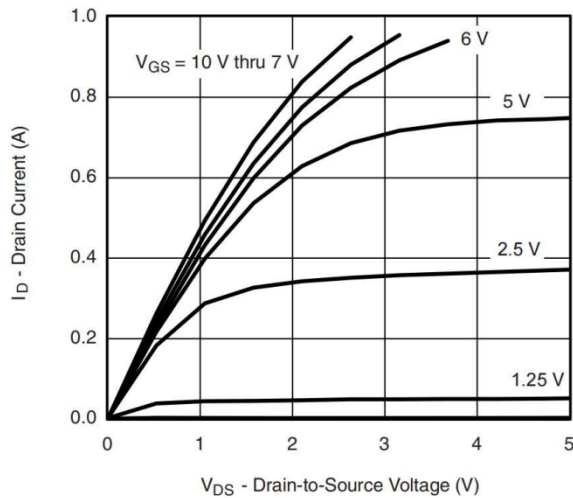
- The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz.copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ . The value in any given application depends on the user is specific board design. The power dissipation is based on the  $t \leq 10\text{s}$  thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation  $P_D$  is based on  $T_{J(MAX)}=150^{\circ}\text{C}$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

**➤ Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)**

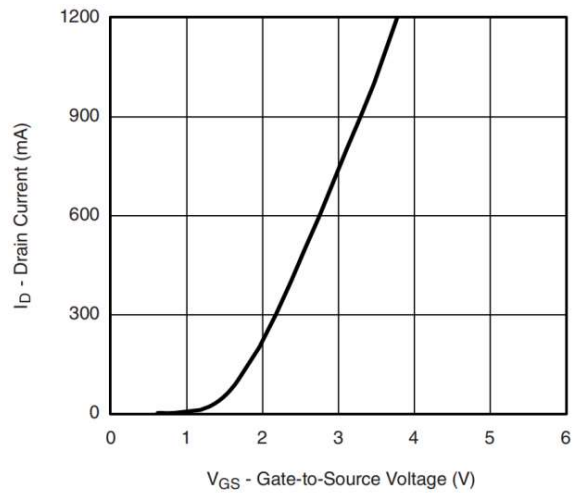
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250uA	60			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250uA	0.75	1	1.25	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.5A		1.1	2.5	Ω
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 0.5A		1.5	3.5	
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 0.5A		1.7	4	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V			1	μA
Gate-Source Leak Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±15V, V <sub>DS</sub> = 0V			±10	μA
Transconductance	G <sub>FS</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.2A		0.1		S
Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = 0.2A			1.3	V
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1MHz		30		pF
Output Capacitance	C <sub>OSS</sub>			6		
Reverse Transfer Capacitance	C <sub>RSS</sub>			2.9		
Turn-on Delay Time	T <sub>D(ON)</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 100mA		25		ns
Rise Time	Tr			10		
Turn-off Delay Time	T <sub>D(OFF)</sub>			35		
Fall Time	Tf			20		
Total Gate Charge	QG	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =0.2A		0.4		nC
Gate Source Charge	QGS			0.1		
Gate Drain Charge	QGD			0.11		



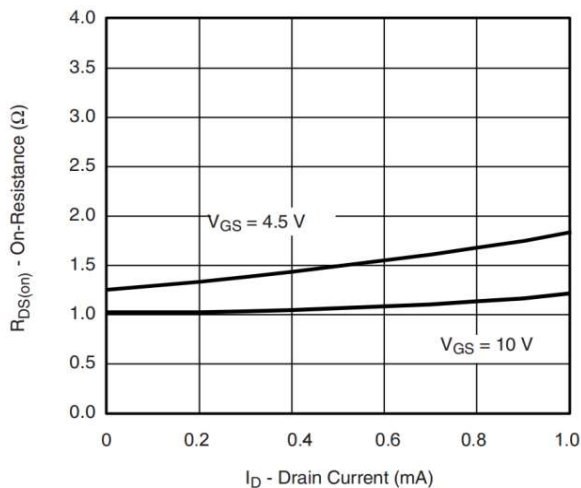
## ➤ Typical Performance Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)



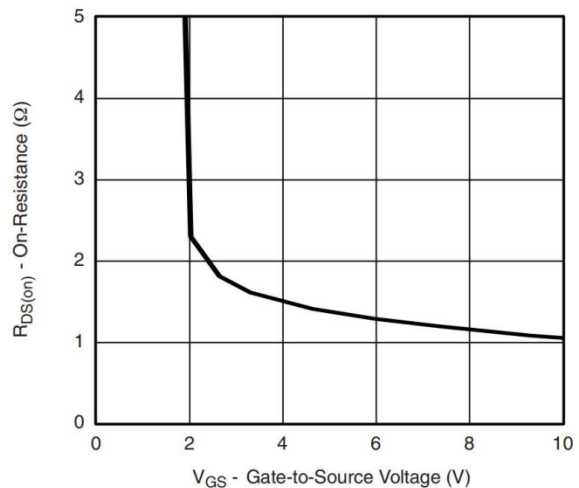
Output Characteristics



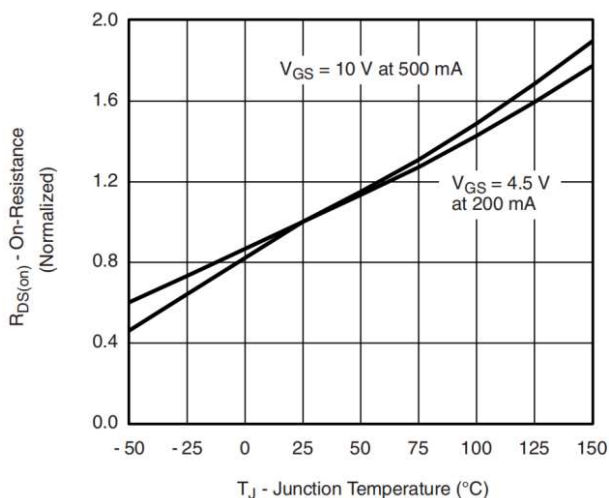
Transfer Characteristics



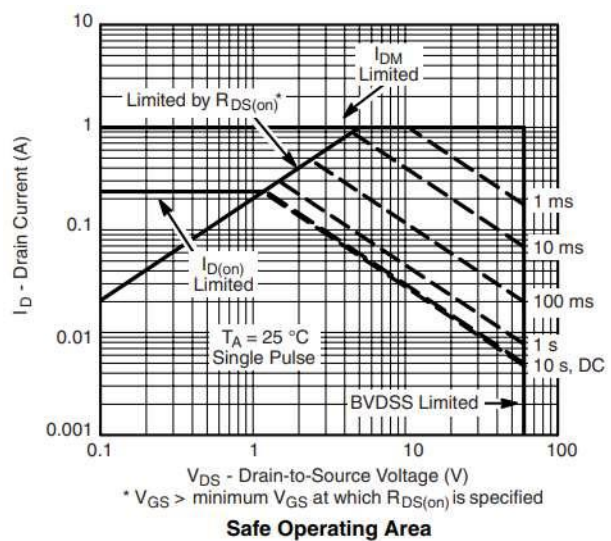
On-Resistance vs. Drain Current



On-Resistance vs. Gate-Source Voltage

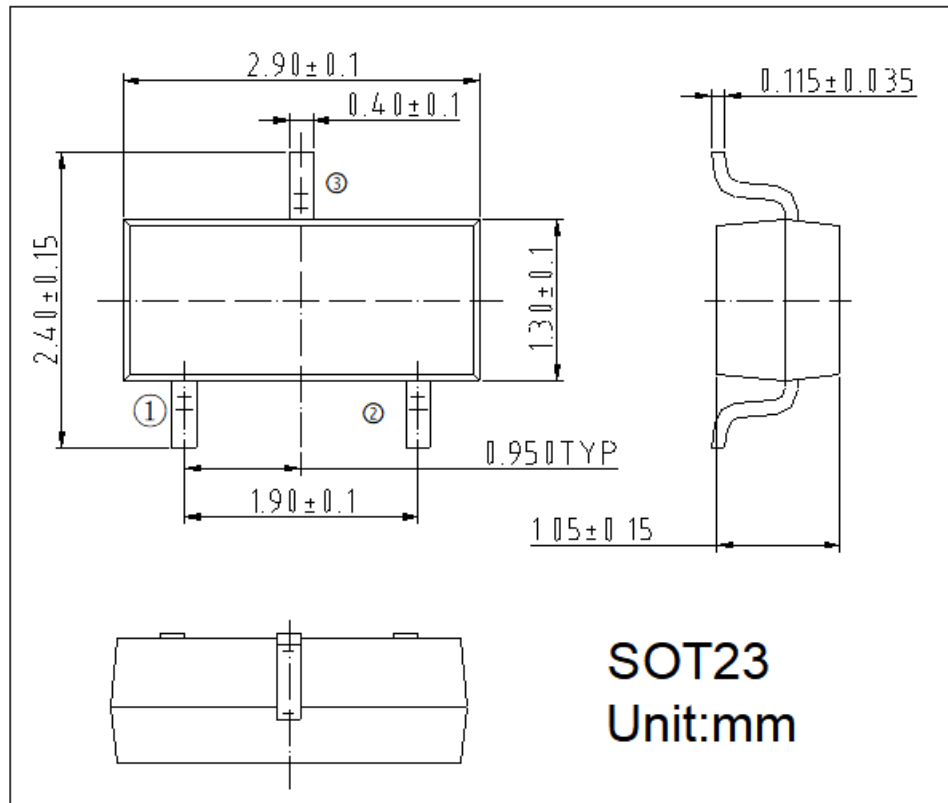


On-Resistance vs. Junction Temperature



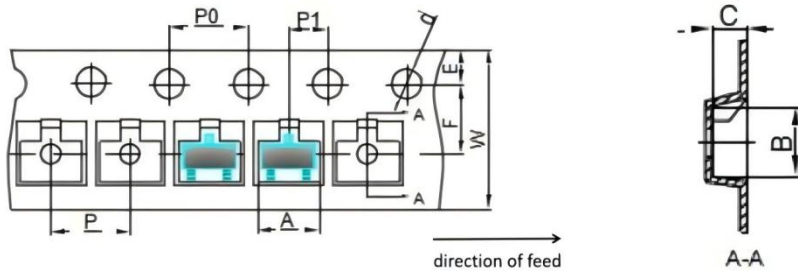
Safe Operating Area

## ➤ Package Information



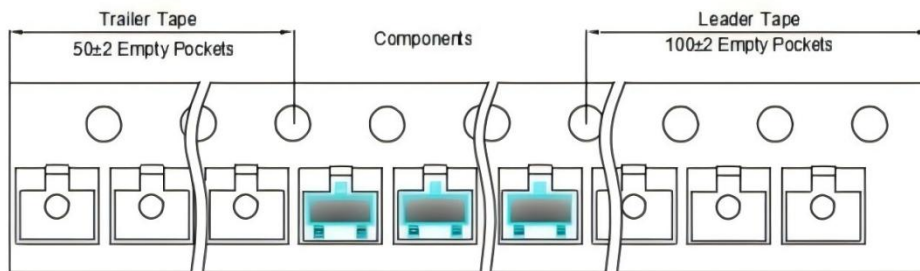
## ➤ SOT-23 Tape and reel

### SOT-23 Embossed Carrier Tape



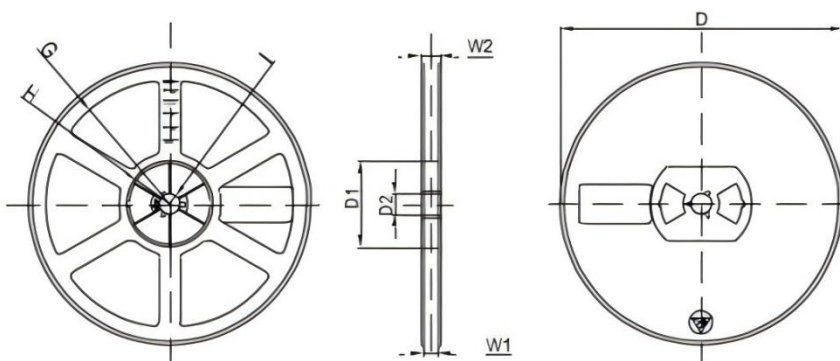
Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15±0.1	2.77±0.1	1.22±0.1	Ø1.50	1.75±0.1	3.5±0.05	4.0±0.1	4.0±0.1	2±0.05	8±0.1

### SOT-23 Tape Leader and Trailer



SOT23 带尾(空封 40 格)、带头 (空封 100 格) 空封数

### SOT-23 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7"Dia	Ø178.00	Ø54±0.2	13.3±0.2	R79.00	R26.00	R6.50±0.2	9±0.5	12±0.5



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